

Computer Architecture

Week 5: Memory



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Course Plan

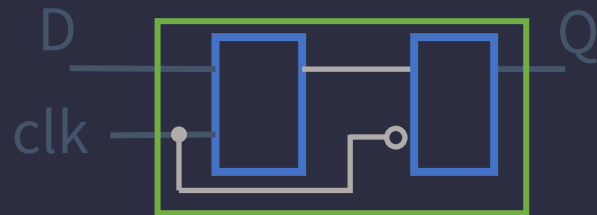
- Memory

Goals for today

Memory

- CPU: Register Files (i.e. Memory w/in the CPU)
- Scaling Memory: Tri-state devices
- Cache: SRAM (Static RAM—random access memory)
- Memory: DRAM (Dynamic RAM)

Last time: How do we store one bit

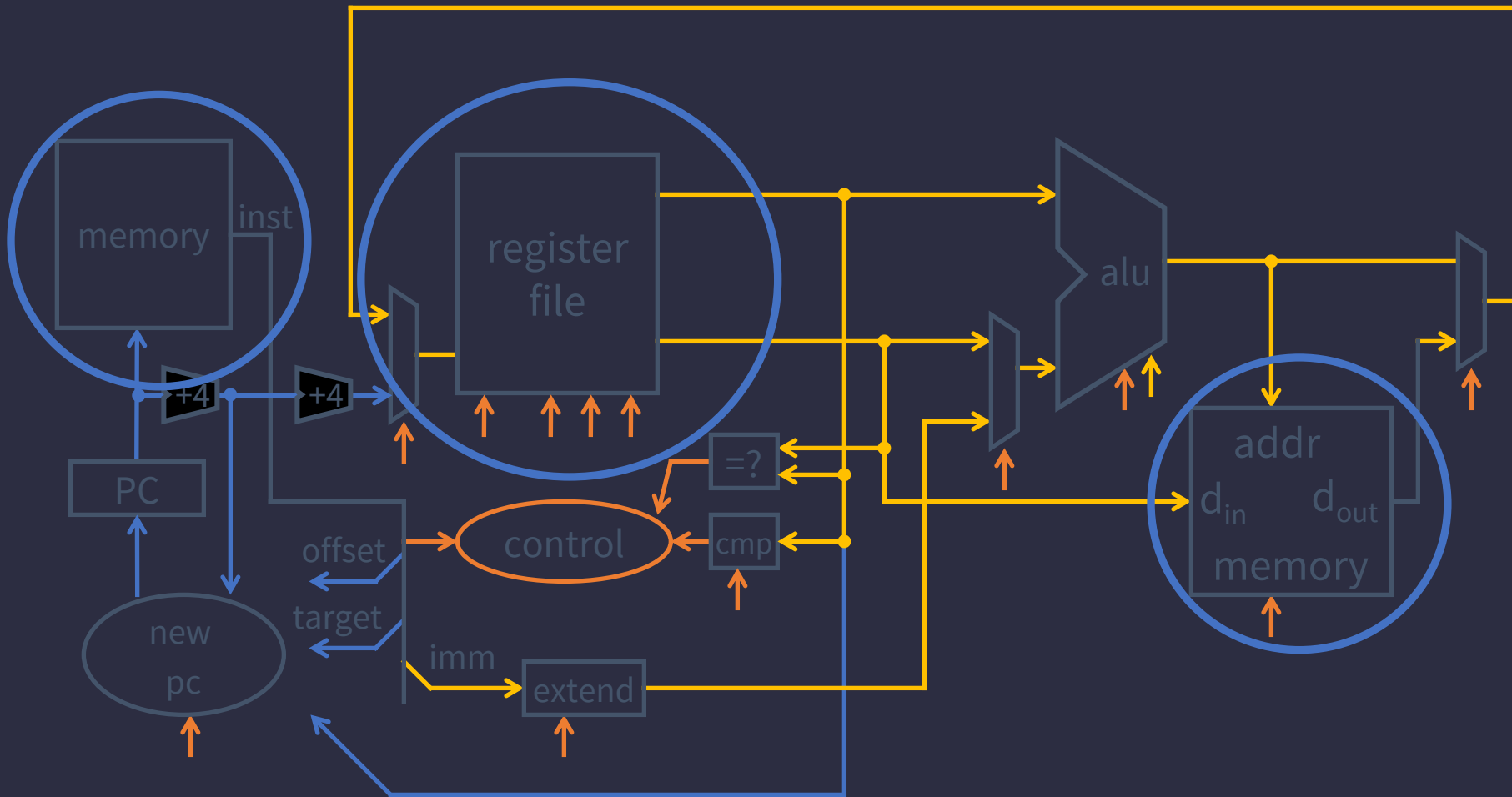


D Flip Flop stores 1 bit

Goal for today

How do we store results from ALU computations?

Big Picture: Building a Processor



A Single cycle processor

Goal for today

How do we store results from ALU computations?

How do we use stored results in subsequent operations?

Register File

How does a Register File work? How do we design it?

Register File

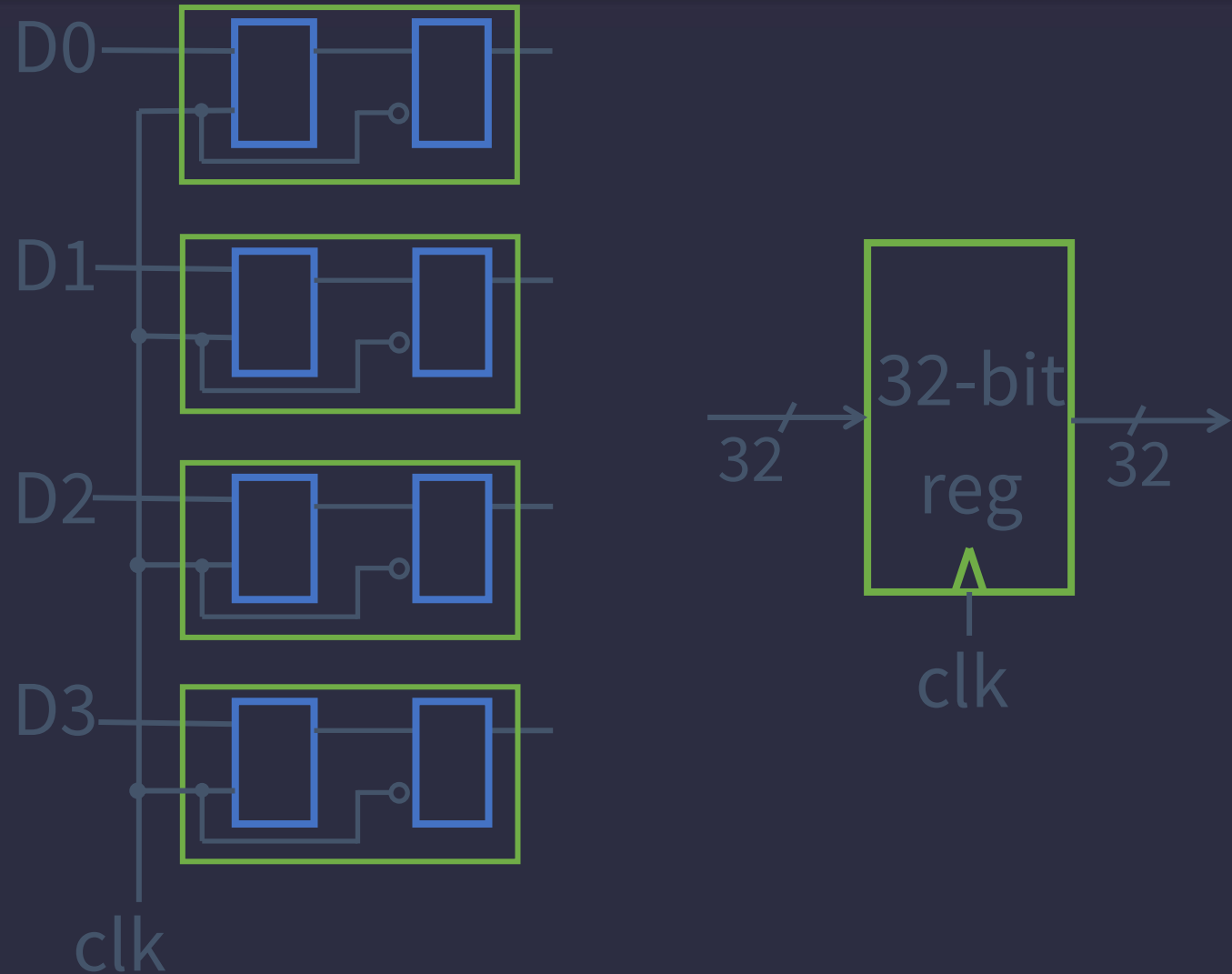
Register File

- N read/write registers
- Indexed by register number



Register File

- D flip-flops in parallel
- shared clock
- extra clocked inputs: write_enable, reset, ...



Register File

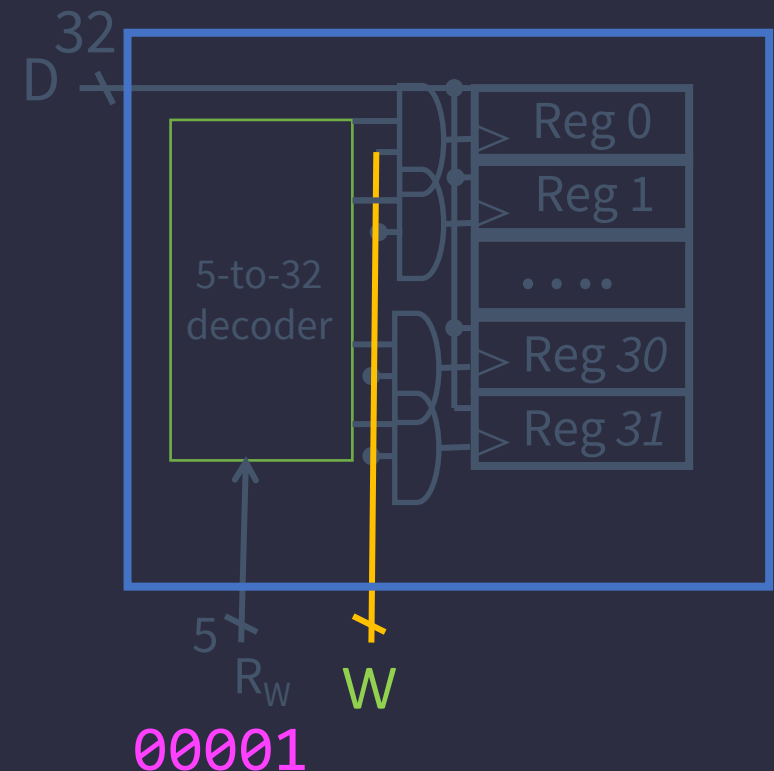
Register File

- N read/write registers
- Indexed by register number

Addi **x1**, x0, 10

How to write to *one* register in the register file?

- Need a decoder



Register File

Register File

- N read/write registers
- Indexed by register number

Implementation:

- D flip flops to store bits
- Decoder for each write port
- Mux for each read port



Tradeoffs

Register File tradeoffs

- + Very fast (a few gate delays for both read and write)

- + Adding extra ports is straightforward

- Doesn't scale

e.g. 32Mb register file with 32 bit registers

Need 32x 1M-to-1 multiplexor and 32x 20-to-1M decoder

How many logic gates/transistors?

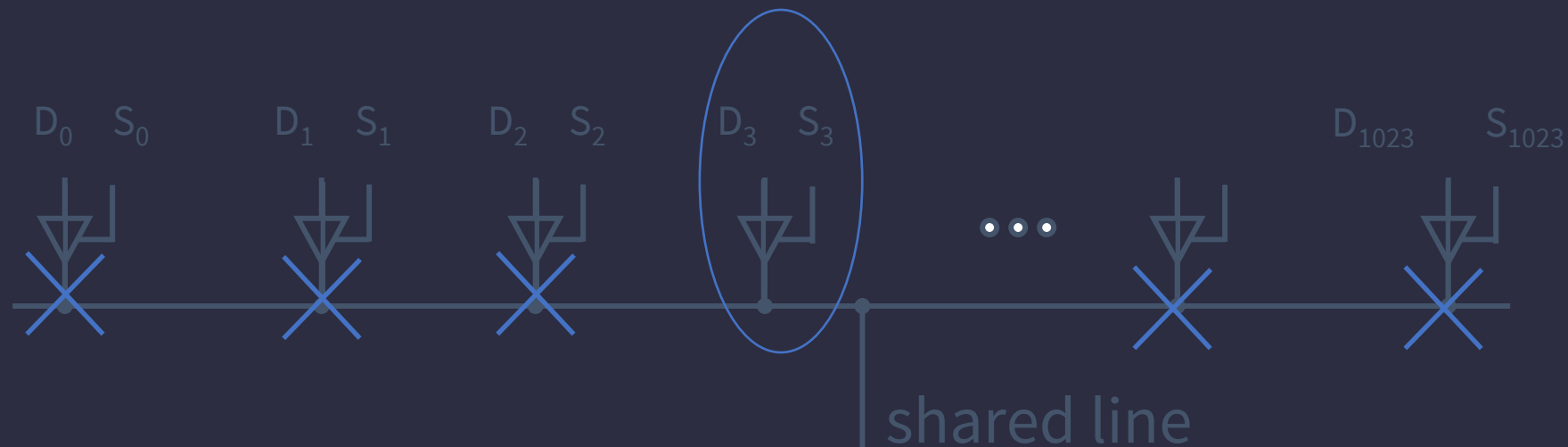
Next Goal

How do we scale/build larger memories?

Building Large Memories

Need a shared bus (or shared bit line)

- Many FlipFlops/outputs/etc. connected to single wire
- Only one output *drives* the bus at a time



- How do we build such a device?

Tri-State Devices

Tri-State Buffers

- If enabled ($E=1$), then $Q = D$
- Otherwise, Q is not connected ($z = \text{high impedance}$)

E	D	Q
0	0	z
0	1	z
1	0	0
1	1	1



Tri-State Devices

Tri-State Buffers

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Tri-State Devices

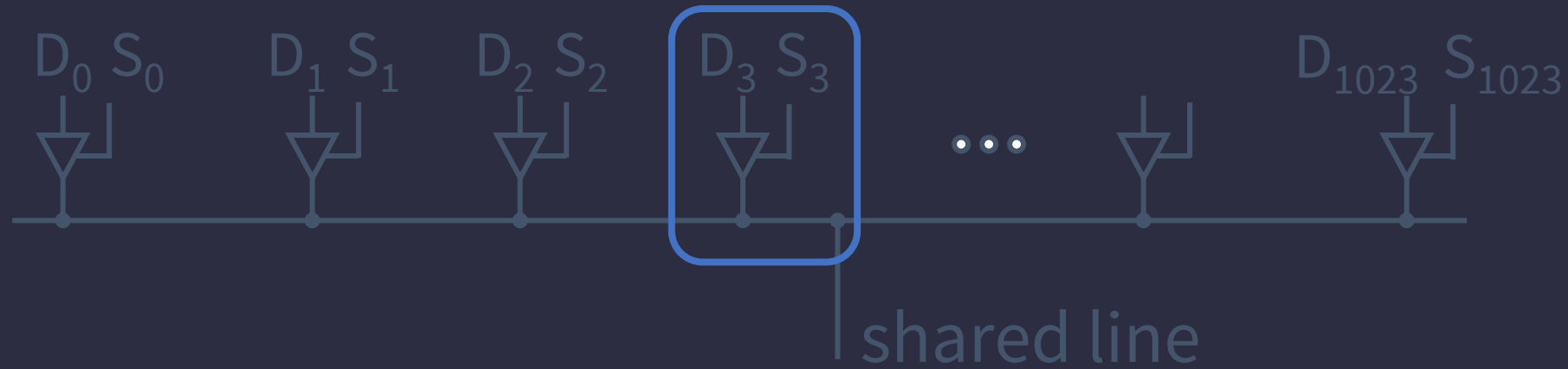
Tri-State Buffers

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Shared Bus



Next Goal

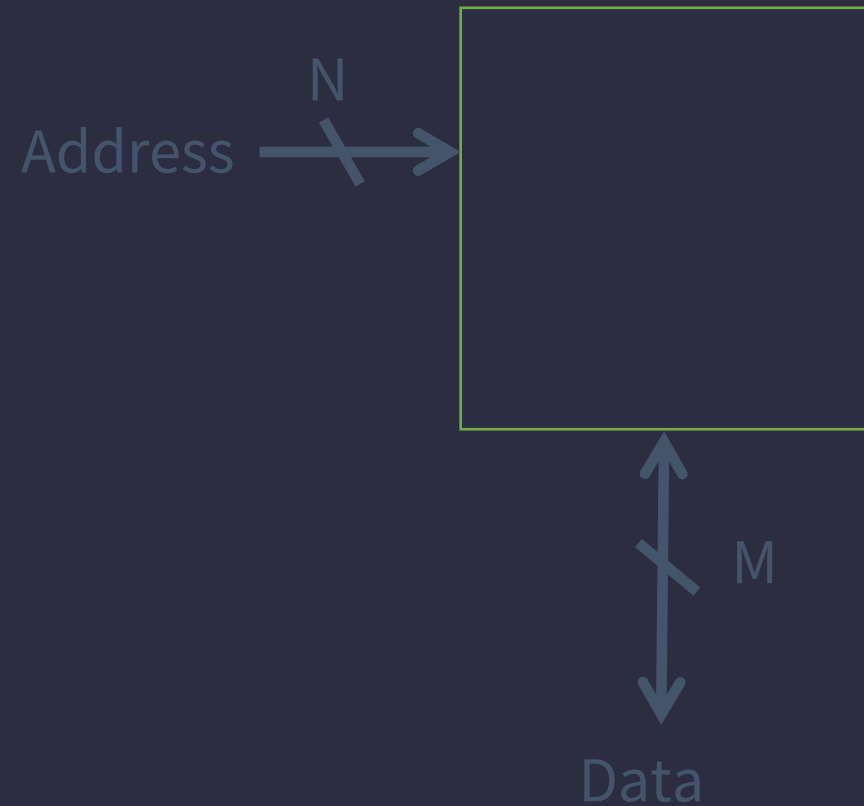
How do we build large memories?

Use similar designs as Tri-state Buffers to connect multiple registers to output line. Only one register will drive output line.

Memory

- Storage Cells + bus
- Inputs: Address, Data (for writes)
- Outputs: Data (for reads)
- Also need R/W signal (not shown)

- N address bits $\rightarrow 2^N$ words total
- M data bits \rightarrow each word M bits

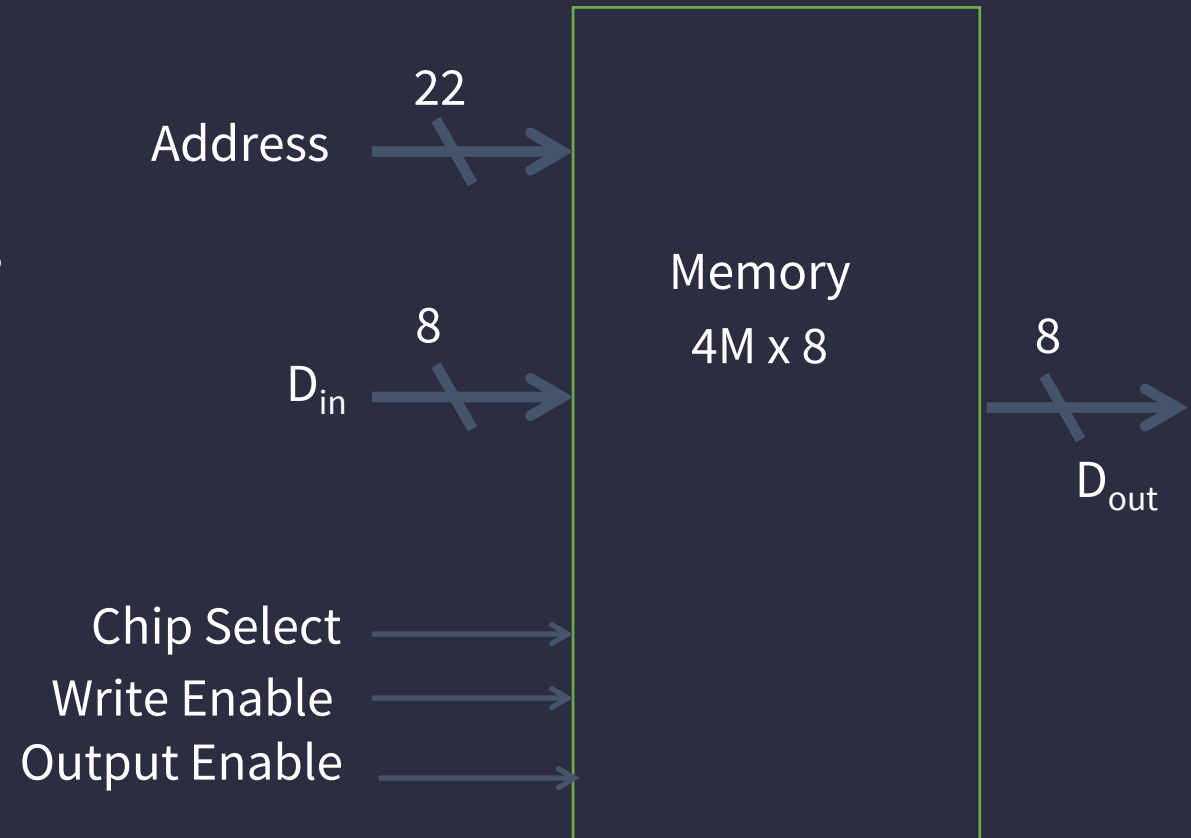


Memory

- Storage Cells + bus
- Decoder selects a word line
- R/W selector determines access type
- Word line is then coupled to the data lines

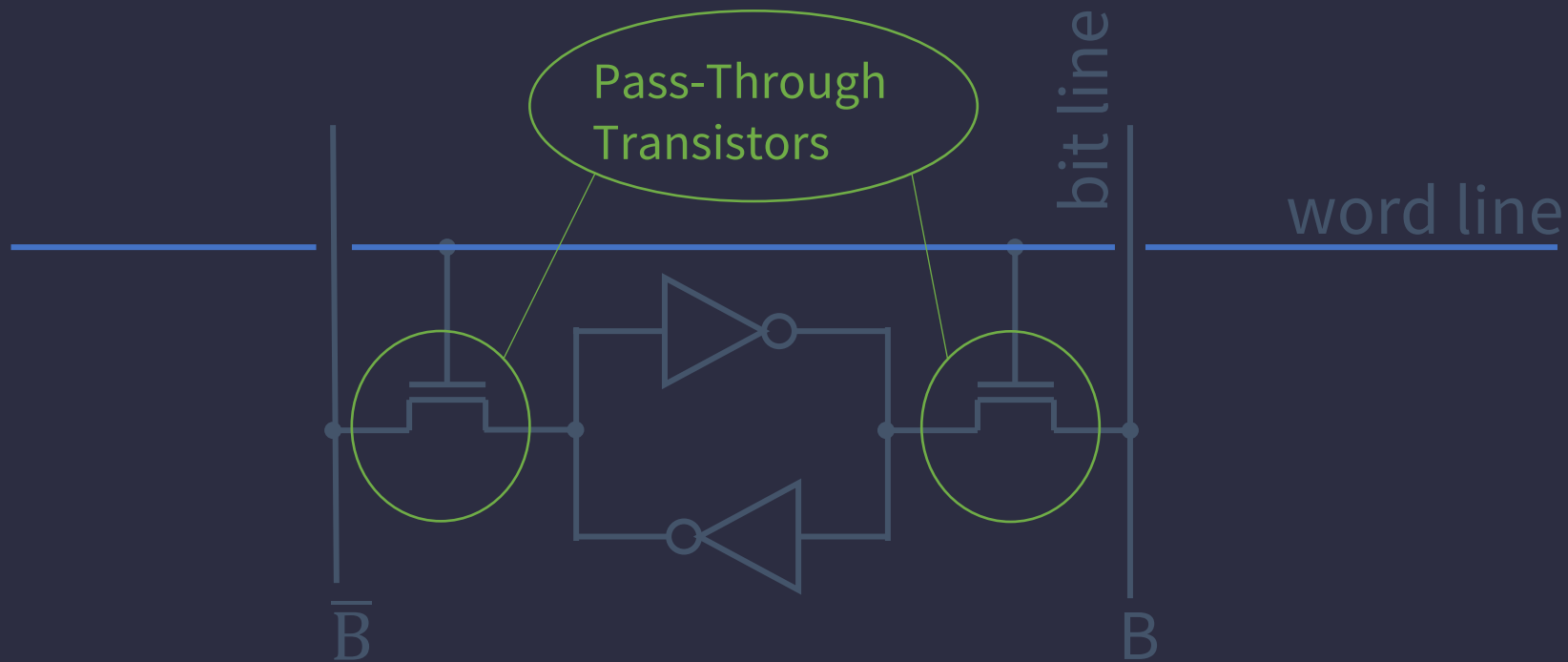
Memory

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SRAM Cell

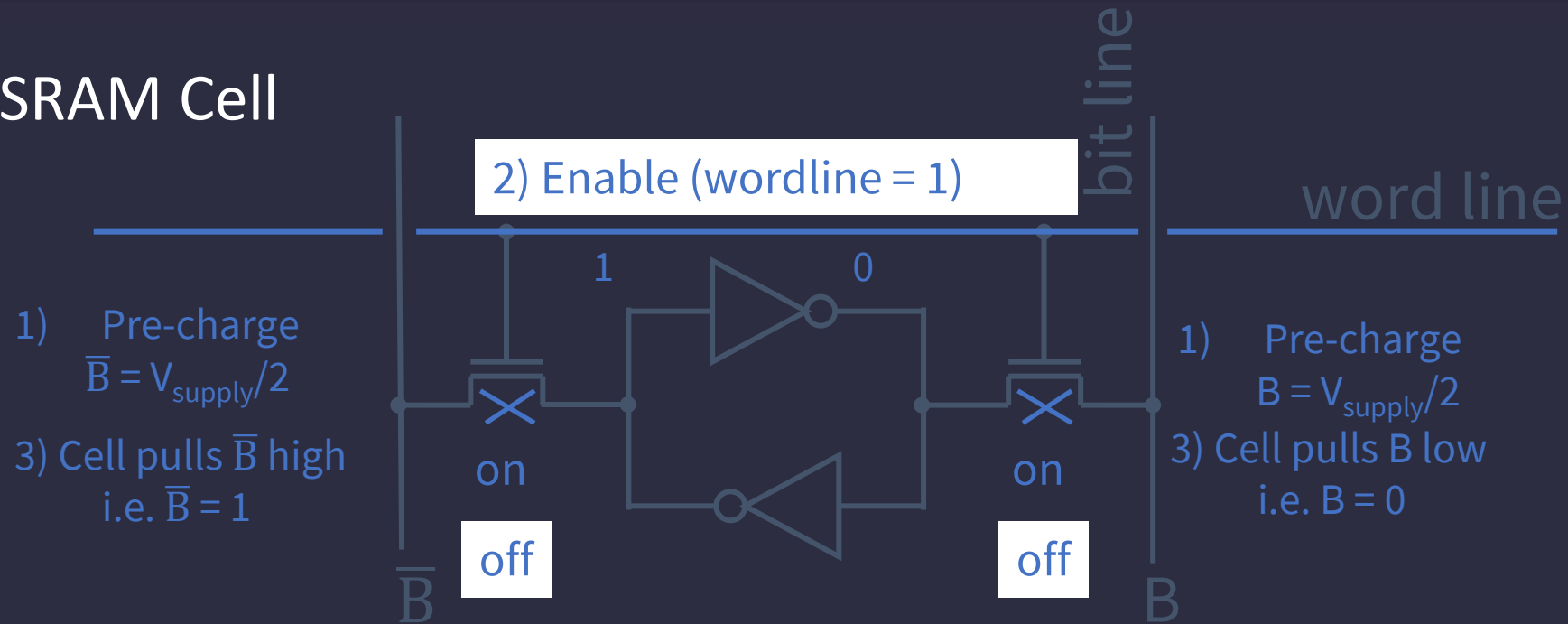
Typical SRAM Cell



Each cell stores one bit, and requires 4 – 8 transistors (6 is typical)

SRAM Cell

Typical SRAM Cell



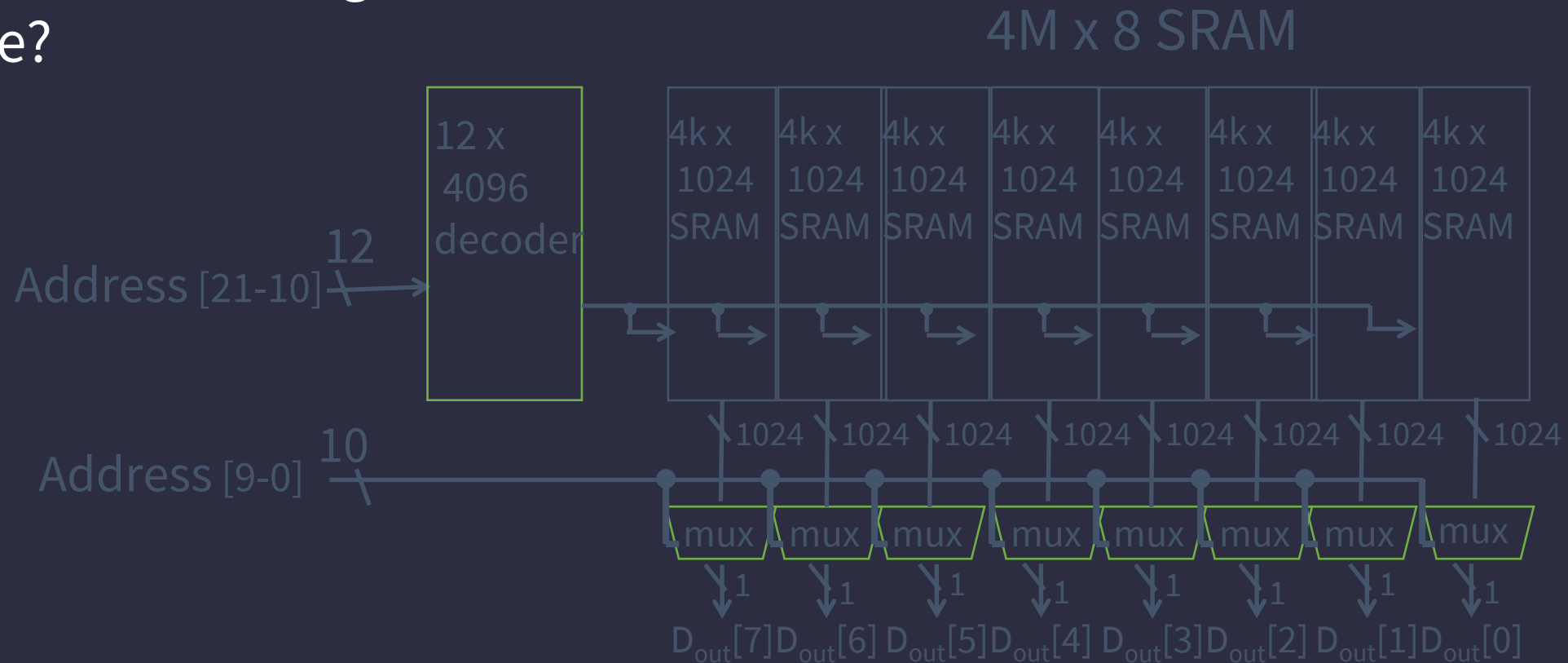
Each cell stores one bit, and requires 4 – 8 transistors (6 is typical)

Read:

- pre-charge B and \bar{B} to $V_{\text{supply}}/2$
- pull word line high
- cell pulls B or \bar{B} low, sense amp detects voltage difference

SRAM

E.g. How do we design a **4M x 8** SRAM Module?



SRAM Summary

SRAM

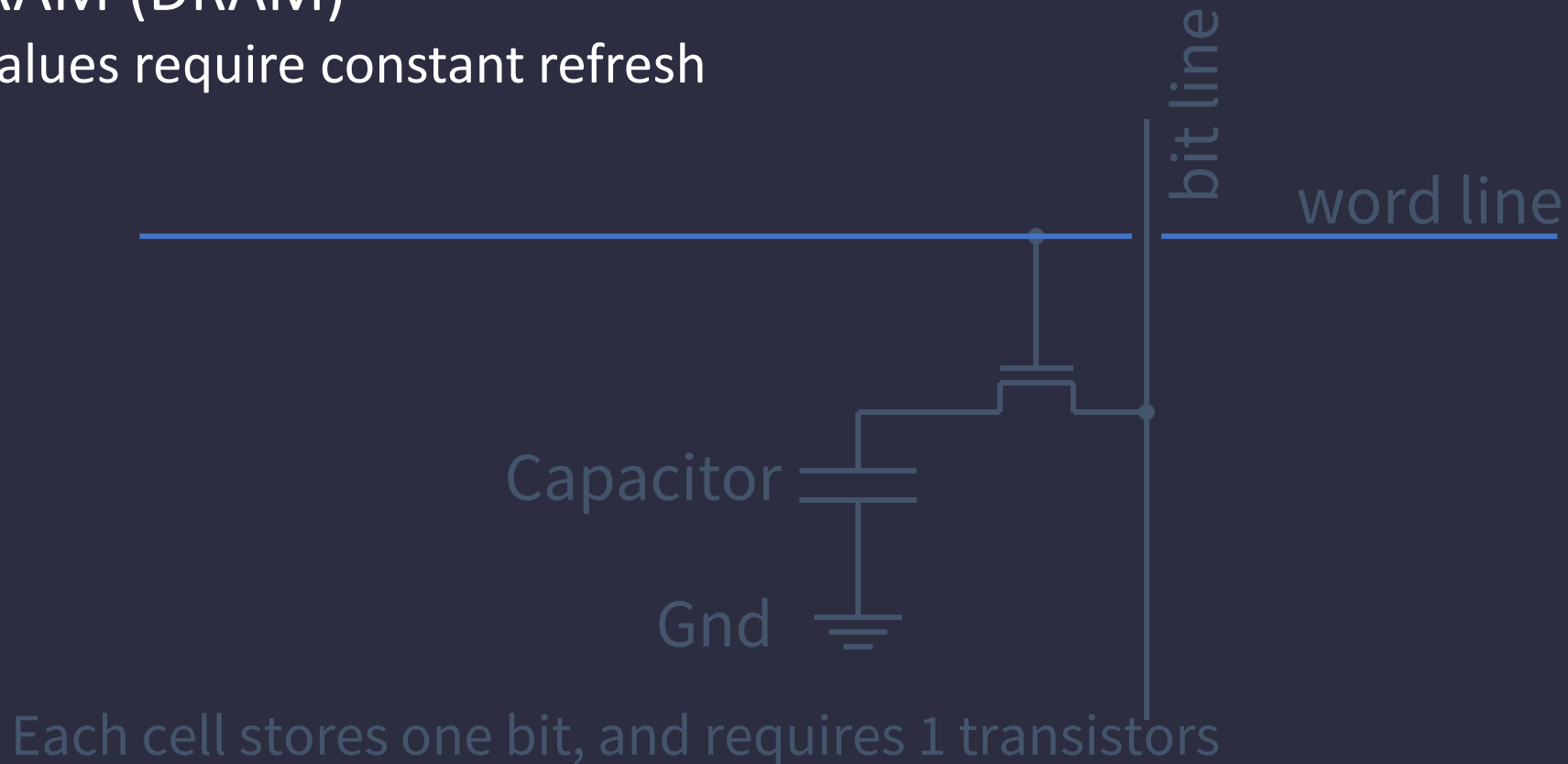
- A few transistors (~ 6) per cell
- Used for working memory (caches)

- But for even higher density...

Dynamic RAM: DRAM

Dynamic-RAM (DRAM)

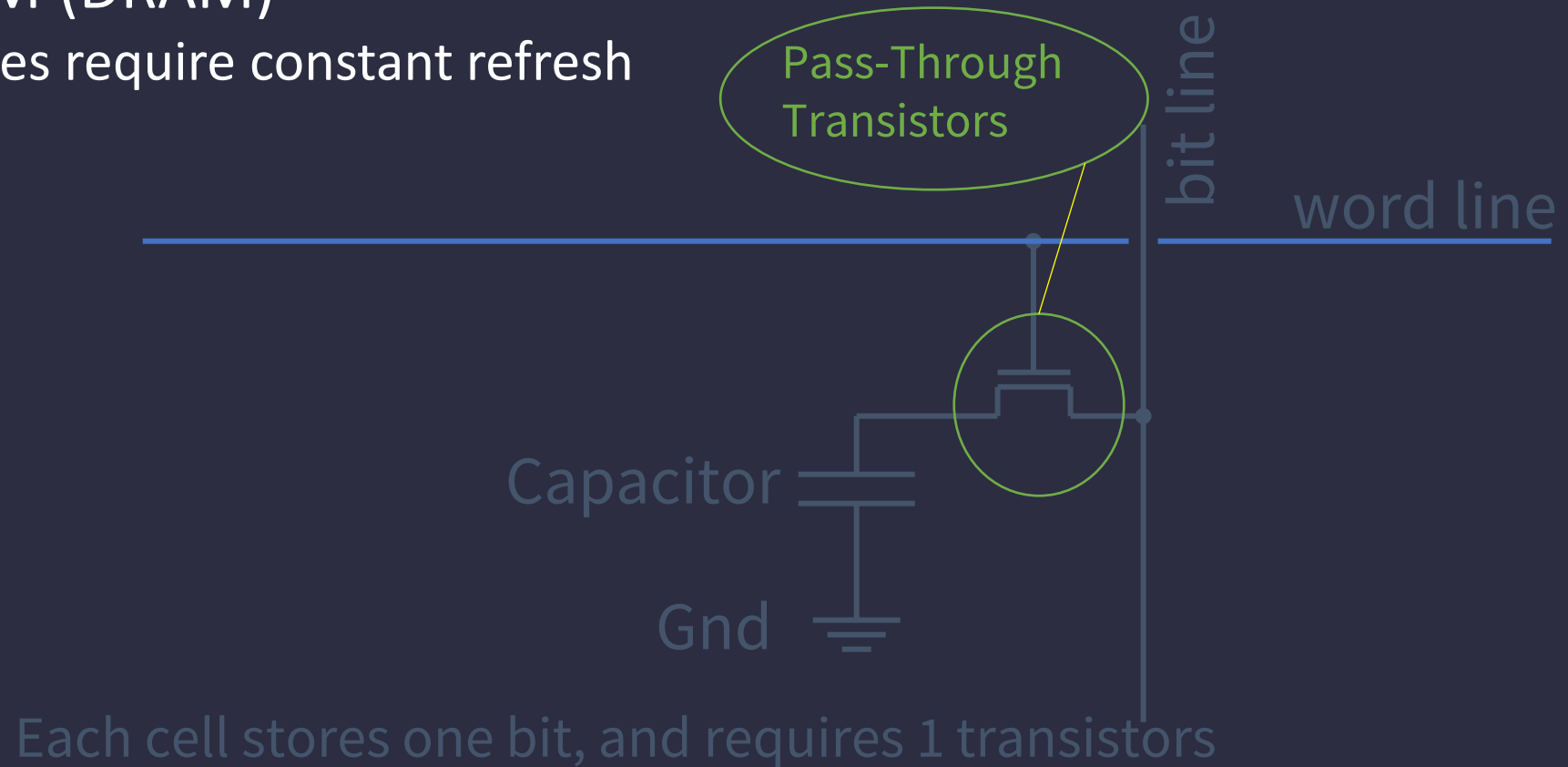
- Data values require constant refresh



Dynamic RAM: DRAM

Dynamic-RAM (DRAM)

- Data values require constant refresh



DRAM vs. SRAM

Single transistor vs. many gates

- Denser, cheaper (\$30/1GB vs. \$30/2MB)
- But more complicated, and has analog sensing

Also needs refresh

- Read and write back...
- ...every few milliseconds
- Organized in 2D grid, so can do rows at a time
- Chip can do refresh internally

Hence... slower and energy inefficient

Memory

Register File tradeoffs

- + Very fast (a few gate delays for both read and write)
- + Adding extra ports is straightforward
- Expensive, doesn't scale
- Volatile

Volatile Memory alternatives: SRAM, DRAM, ...

- Slower
- + Cheaper, and scales well
- Volatile

Non-Volatile Memory (NV-RAM): Flash, EEPROM, ...

- + Scales well
- Limited lifetime; degrades after 100000 to 1M writes